

E1  
<sup>21</sup>46. (amended) The construction of claim <sup>18</sup>43 wherein the conductive layer is on the first electrode.

<sup>22</sup>47. (amended) The construction of claim <sup>18</sup>43 wherein the conductive layer comprises elemental metal, a metal alloy, or a metal containing compound.

<sup>25</sup>50. (new) The construction of claim <sup>26</sup>26 wherein the substrate comprises a semiconductive wafer.

E2  
<sup>26</sup>51. (new) The construction of claim <sup>26</sup>26 wherein the first capacitor electrode comprises HSG polysilicon.

<sup>27</sup>52. (new) The construction of claim <sup>26</sup>51, wherein the atomic layer deposited barrier layer comprises TiN and the first capacitor electrode further comprises the TiN.

<sup>28</sup>53. (new) The construction of claim <sup>26</sup>26 wherein the atomic layer deposited barrier layer comprises TiN.

<sup>29</sup>54. (new) The construction of claim <sup>26</sup>26 wherein the capacitor dielectric layer comprises Al<sub>2</sub>O<sub>3</sub>.

<sup>30</sup>55. (new) The construction of claim <sup>26</sup>26 wherein the second capacitor electrode comprises TiN.

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56. (new) The construction of claim 28 wherein the first capacitor electrode comprises HSG polysilicon, the atomic layer deposited barrier layer comprises TiN, the capacitor dielectric layer comprises  $Al_2O_3$ , and the second capacitor electrode comprises TiN.

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57. (new) The construction of claim 31 wherein the substrate comprises a semiconductive wafer.

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58. (new) The construction of claim 31 wherein the first capacitor electrode comprises HSG polysilicon.

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59. (new) The construction of claim 58, wherein the barrier layer comprises TiN and the first capacitor electrode further comprises the TiN.

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60. (new) The construction of claim 31 wherein the barrier layer comprises TiN.

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61. (new) The construction of claim 31 wherein the capacitor dielectric layer comprises  $Al_2O_3$ .

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62. (new) The construction of claim 31 wherein the second capacitor electrode comprises TiN.

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63. (new) The construction of claim 31 wherein the first capacitor electrode comprises HSG polysilicon, the barrier layer comprises TiN, the capacitor dielectric layer comprises  $Al_2O_3$ , and the second capacitor electrode comprises TiN.

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64. (new) The construction of claim 38 wherein the substrate comprises a semiconductive wafer.

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65. (new) The construction of claim 38 wherein the first capacitor electrode comprises HSG polysilicon.

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66. (new) The construction of claim 65, wherein the atomic layer deposited conductive layer comprises TiN and the first capacitor electrode further comprises the TiN.

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67. (new) The construction of claim 38 wherein the atomic layer deposited conductive layer comprises TiN.

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68. (new) The construction of claim 38 wherein the capacitor dielectric layer comprises Al<sub>2</sub>O<sub>3</sub>.

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69. (new) The construction of claim 38 wherein the second capacitor electrode comprises TiN.

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70. (new) The construction of claim 38 wherein the first capacitor electrode comprises HSG polysilicon, the atomic layer deposited conductive layer comprises TiN, the capacitor dielectric layer comprises Al<sub>2</sub>O<sub>3</sub>, and the second capacitor electrode comprises TiN.

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71. (new) The construction of claim 43 wherein the substrate comprises a semiconductive wafer.

*41*  
72. (new) The construction of claim <sup>18</sup>43 wherein the first capacitor electrode comprises HSG polysilicon.

*48*  
73. (new) The construction of claim <sup>48</sup>72, wherein the conductive layer comprises TiN and the first capacitor electrode further comprises the TiN.

*49*  
74. (new) The construction of claim <sup>18</sup>43 wherein the conductive layer comprises TiN.

*50*  
75. (new) The construction of claim <sup>18</sup>43 wherein the capacitor dielectric layer comprises Al<sub>2</sub>O<sub>3</sub>.

*51*  
76. (new) The construction of claim <sup>18</sup>43 wherein the second capacitor electrode comprises TiN.

*52*  
77. (new) The construction of claim <sup>18</sup>43 wherein the first capacitor electrode comprises HSG polysilicon, the conductive layer comprises TiN, the capacitor dielectric layer comprises Al<sub>2</sub>O<sub>3</sub>, and the second capacitor electrode comprises TiN.